20V N-Channel Enhancement Mode MOSFET

The JXP3416EVRG uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and high density cell Design for ultra low on-resistance. This device is suitable for use as a load switch or in PWM applications.

V_{DS} =20V I_D =6.5A
$R_{DS(ON)}$(Typ.)=18 @V_{GS}=2.5V
$R_{DS(ON)}$(Typ.)=15 @V_{GS}=4.5V
High power and current handing capability
Lead free product is acquired
Surface mount package
ESD Rating: 3500V HBM

PWM applications
Load switch

SOT-23

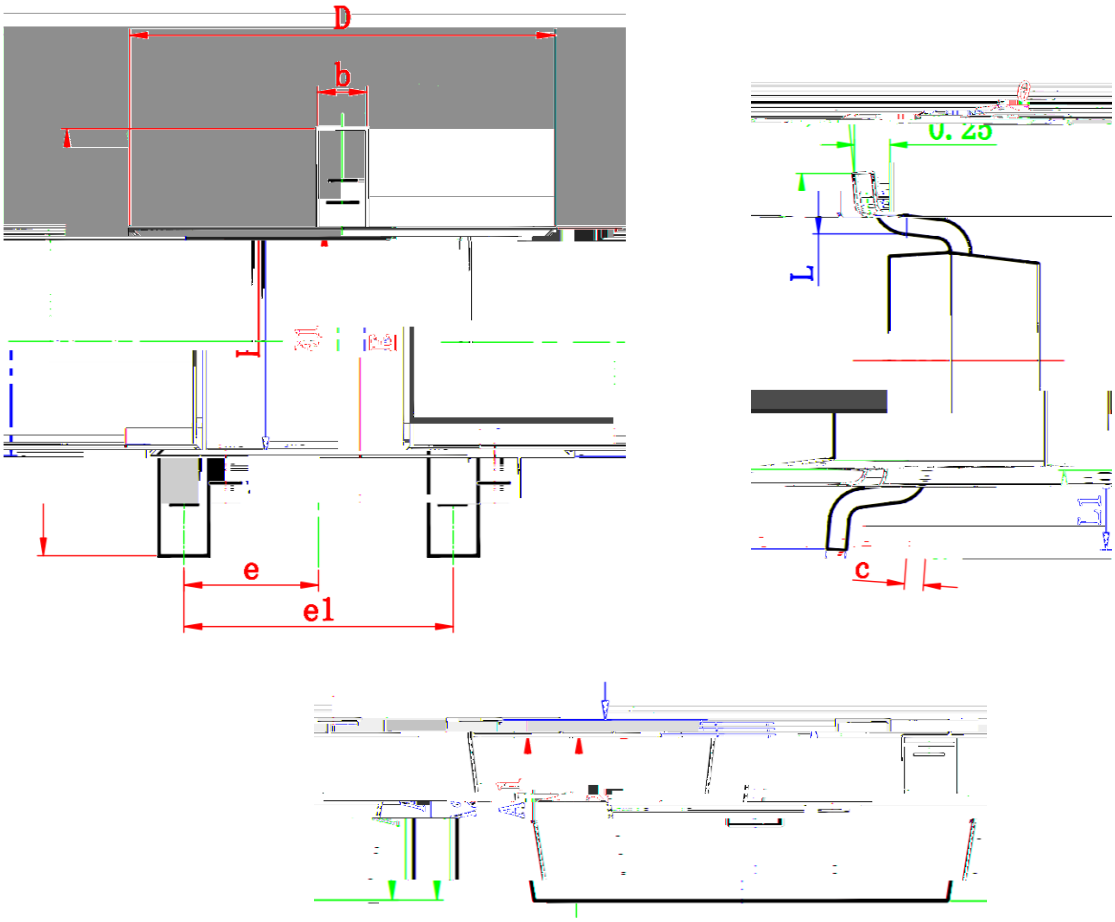
Part Number	Storage Temperature	Package	Marking	Devices Per Reel
JXP3416ERG	-55°C to +150°C	SOT-23	3416E	3000

(TA=25 unless otherwise noted)

parameter	symbol	limit	unit

Parameter	Symbol	

SOT-23



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100		